



ZXMN6A09GTA Information

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Part Number ZXMN6A09GTA

Manufacturer Diodes Incorporated

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 60V 6.9A SOT223

Package TO-261-4, TO-261AA

For the pricing/inventory/lead time, please contact

us

For Reference Only

Website: https://www.heisener.com
E-mail: salesdept@heisener.com



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ZXMN6A09GTA Specifications

Manufacturer Part Number ZXMN6A09GTA Manufacturer Diodes Incorporated Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-261-4, TO-261AA Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 5.4A (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3V @ 250µA Gate Charge (Qg) (Max) @ Vgs 24.2nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 1407pF @ 40V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2W (Ta) Rds On (Max) @ Id, Vgs 40 mOhm @ 8.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-223 Package / Case TO-261-4, TO-261AA Report errors?		
Category Discrete Semiconductor Products Package TO-261-4, TO-261AA Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 5.4A (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3V @ 250µA Gate Charge (Qg) (Max) @ Vgs 24.2nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 1407pF @ 40V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2W (Ta) Rds On (Max) @ Id, Vgs 40 mOhm @ 8.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-223 Package / Case TO-261-4, TO-261AA	Manufacturer Part Number	ZXMN6A09GTA
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Series-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C5.4A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs24.2nC @ 5VInput Capacitance (Ciss) (Max) @ Vds1407pF @ 40VVgs (Max)±20VFET Feature-Power Dissipation (Max)2W (Ta)Rds On (Max) @ Id, Vgs40 mOhm @ 8.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223Package / CaseTO-261-4, TO-261AA		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C5.4A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs24.2nC @ 5VInput Capacitance (Ciss) (Max) @ Vds1407pF @ 40VVgs (Max)±20VFET Feature-Power Dissipation (Max)2W (Ta)Rds On (Max) @ Id, Vgs40 mOhm @ 8.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223Package / CaseTO-261-4, TO-261AA	Package	TO-261-4, TO-261AA
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C5.4A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs24.2nC @ 5VInput Capacitance (Ciss) (Max) @ Vds1407pF @ 40VVgs (Max)±20VFET Feature-Power Dissipation (Max)2W (Ta)Rds On (Max) @ Id, Vgs40 mOhm @ 8.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223Package / CaseTO-261-4, TO-261AA	Series	-
Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C5.4A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs24.2nC @ 5VInput Capacitance (Ciss) (Max) @ Vds1407pF @ 40VVgs (Max)±20VFET Feature-Power Dissipation (Max)2W (Ta)Rds On (Max) @ Id, Vgs40 mOhm @ 8.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223Package / CaseTO-261-4, TO-261AA	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3V @ 250μA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1407pF @ 40V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 40 mOhm @ 8.2A, 10V Operating Temperature Supplier Device Package Package / Case 5.4A (Ta) 6.4.4 (Ta) 5.4.4 (Ta) 5.4.4 (Ta) 6.4.4 (Ta) 5.4.4 (Ta) 5.4.4 (Ta) 6.4.4 (Ta) 5.4.4 (Ta) 5.4.4 (Ta) 5.4.4 (Ta) 6.4.4 (Ta) 5.4.4 (Ta) 5.4.4 (Ta) 6.4.4 (Ta) 5.4.4 (Ta) 6.4.4 (Ta) 6.4	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 3V @ 250μA Gate Charge (Qg) (Max) @ Vgs 1407pF @ 40V Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Au mOhm @ 8.2A, 10V Operating Temperature Surplier Device Package Package / Case 10V 3V @ 250μA 24.2nC @ 5V 1407pF @ 40V 24.2nC @ 5V 1407pF @ 40V 24.2nC @ 5V 1407pF @ 40V 40 mOhm @ 8.2A, 10V CTJ) Surface Mount Surface Mount	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Surplier Device Package Package / Case 3V @ 250μA 24.2nC @ 5V 1407pF @ 40V 240V 250V FET Feature	Current - Continuous Drain (Id) @ 25°C	5.4A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1407pF @ 40V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 40 mOhm @ 8.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case TO-261-4, TO-261AA	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Mounting Type Surface Mount Supplier Device Package Package / Case 1407pF @ 40V 20V 40 W Ta) 40 mOhm @ 8.2A, 10V Surface Mount Surface Mount Surface Mount	Vgs(th) (Max) @ Id	3V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)2W (Ta)Rds On (Max) @ Id, Vgs40 mOhm @ 8.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223Package / CaseTO-261-4, TO-261AA	Gate Charge (Qg) (Max) @ Vgs	24.2nC @ 5V
FET Feature - Power Dissipation (Max) 2W (Ta) Rds On (Max) @ Id, Vgs 40 mOhm @ 8.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-223 Package / Case TO-261-4, TO-261AA	Input Capacitance (Ciss) (Max) @ Vds	1407pF @ 40V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 40 mOhm @ 8.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case TO-261-4, TO-261AA	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs40 mOhm @ 8.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-223Package / CaseTO-261-4, TO-261AA	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-223 Package / Case TO-261-4, TO-261AA	Power Dissipation (Max)	2W (Ta)
Mounting Type Surface Mount Supplier Device Package SOT-223 Package / Case TO-261-4, TO-261AA	Rds On (Max) @ Id, Vgs	40 mOhm @ 8.2A, 10V
Supplier Device Package SOT-223 Package / Case TO-261-4, TO-261AA	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-261-4, TO-261AA	Mounting Type	Surface Mount
	Supplier Device Package	SOT-223
Report errors?	Package / Case	TO-261-4, TO-261AA
		Report errors?

ZXMN6A09GTA Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

ZXMN6A09GTA Payment Methods



















ZXMN6A09GTA Shipping Methods













If you have any question about ZXMN6A09GTA, please do not hesitate to contact us!

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